

STB7101

0.9/1.9GHz BROAD BAND PRE-POWER AMPLIFIER

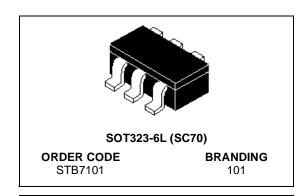
- OPERATING FREQUENCY 900-1900MHz
- OUTPUT POWER 9.8dBm typ. @ 900MHz
 7.5dBm typ. @ 1900MHz
- POWER GAIN $G_P = 20.3 dB$ typ. @ 900MHz $G_P = 20.5 dB$ typ. @ 1900MHz

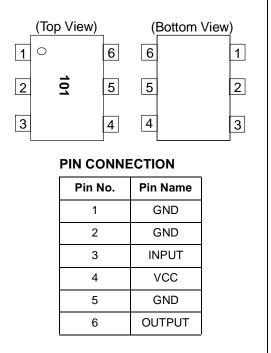


PA driver for cellular applications

DESCRIPTION

The STB7101, designed for cellular applications (0.9/1.9GHz), uses a 20 GHz F_T silicon bipolar process. This IC is a wide range amplifier operating from 900MHz to 1900MHz, in the overall frequencies range the gain flatness is less than 1 dB. The STB7101 is housed in a very small SMD package SOT323-6L.





ABSOLUTE MAXIMUM RATINGS

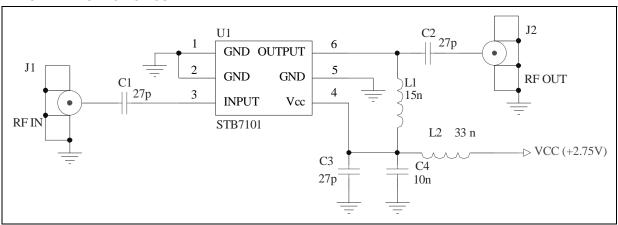
Symbol	Parameter	Conditions	Value	Unit
V _{cc}	Supply voltage	$T_a = +25$ °C, pin 4 and 6	4.5	V
T _{stg}	Storage temperature		-55 to +150	°C
Ta	Operating ambient temperature		-40 to +85	°C
Pin	Input power	T _a = +25 °C	10	dBm

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ELECTRICAL CHARACTERISTICS (Ta = +25°C, Vcc = 2.75V, ZL = Zs = 50 Ω , unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
V _{cc}	Supply voltage		2.6	2.75	3.3	V
I _{cc}	Circuit current	No signal		28		mA
Gp	Power Gain	f = 0.9GHz f = 1.9GHz		20.3 20.5		dB
NF	Noise figure	f = 0.9GHz f = 1.9GHz		5 4.5		dB
P _{1dB}	Output 1dB Compr. Power	f = 0.9GHz f = 1.9GHz		9.8 7.5		dBm
RL _{IN}	Input return loss	f = 0.9GHz f = 1.9GHz		8 6.2		dB
RL _{OUT}	Output Return loss	f = 0.9GHz f = 1.9GHz		9.7 9.7		dB
S ₁₂	Isolation	f = 0.9GHz f = 1.9GHz		-34 -33		dB
P _o (Sat)	Saturated output power level	f = 0.9GHz f = 1.9GHz		11.3 9.7		dBm
OIP3	Output Third Order Intercept	f = 0.9GHz f = 1.9GHz		16.5 14.9		dBm

TYPICAL EVALUATION CIRCUIT



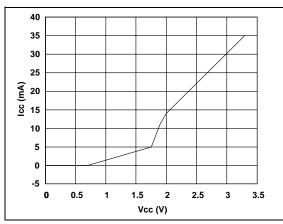
Evaluation circuit components

C1 = C2 = C3 = 27pF
C4 = 10nF
L1 = 15nH
L2 = 33nH

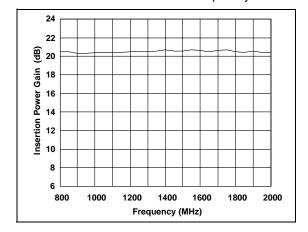
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TYPICAL PERFORMANCE ($T_a = +25$ °C, Vcc = 2.75V, unless otherwise specified)

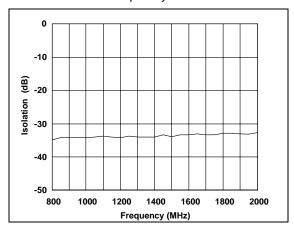
Circuit Current versus Supply Voltage



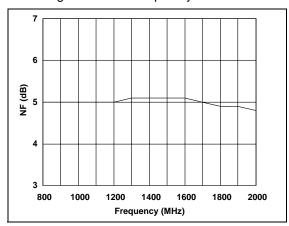
Insertion Power Gain versus Frequency



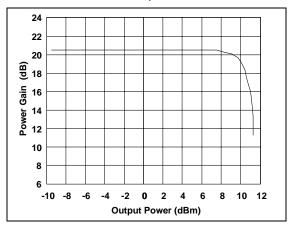
Isolation versus Frequency



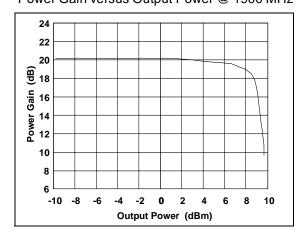
Noise Figure versus Frequency



Power Gain versus Output Power @ 900 MHz

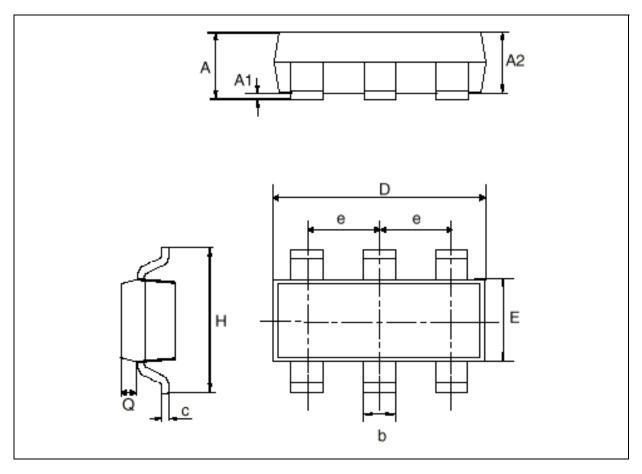


Power Gain versus Output Power @ 1900 MHz



SOT323-6L MECHANICAL DATA

	mm			Inch		
DIM.	MIN.	TYP.	MAX	MIN.	TYP.	MAX
А	0.8		1.1	0.031		0.043
A1	0		0.1	0		0.004
A2	0.8		1	0.0031		0.039
b	0.15		0.3	0.006		0.012
С	0.1		0.18	0.004		0.007
D	1.8		2.2	0.071		0.088
E	1.15		1.35	0.045		0.59
е		0.65			0.025	
Н	1.8		2.4	0.071		0.094
Q	0.1		0.4	0.004		0.016



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